



DCP53/-16

PNP SURFACE MOUNT TRANSISTOR

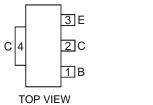
Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DCP56)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)







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Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-1.5	A
Continuous Collector Current	Ic	-1	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = 25°C (Note 3)	P_d	1	W
Operating and Storage Temperature Range	T_j , T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Ambient Air @ T _A = 25°C (Note 3)	$R_{ heta JA}$	125	°C/W

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-100	_		V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	_	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	-100 -20	nA μA	$V_{CB} = -30V, I_{E} = 0$ $V_{CB} = -30V, I_{E} = 0,$ $T_{A} = 150^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	_	-10	μΑ	$V_{EB} = -5V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	-0.5	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn-On Voltage	V _{BE} (ON)	_	_	-1.0	V	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain	h _{FE}	40 25	_	250 —	_	$I_C = -150$ mA, $V_{CE} = -2V$ $I_C = -500$ mA, $V_{CE} = -2V$
DCP53-1	6	100	_	250		$I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	_	200	_	MHz	$I_C = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 100MHz

1. No purposefully added lead. Notes:

Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.



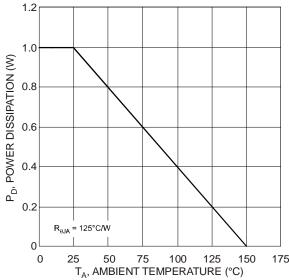


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

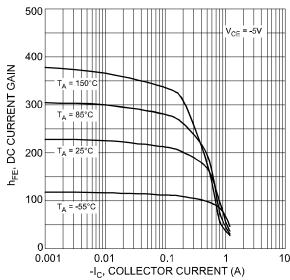


Fig. 3 Typical DC Current Gain vs. Collector Current

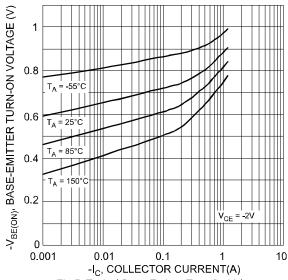


Fig 5. Typical Base-Emitter Turn-On Voltage vs. Collector Current

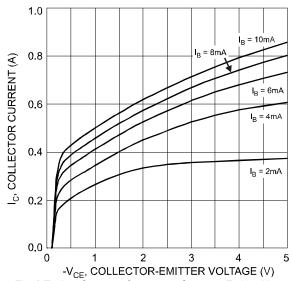


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

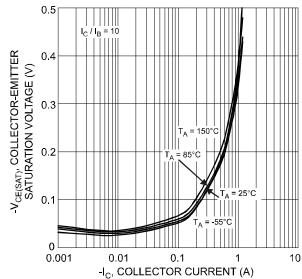


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

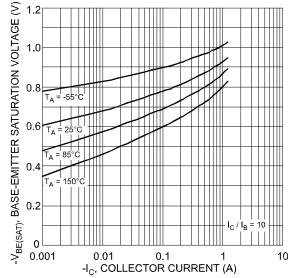
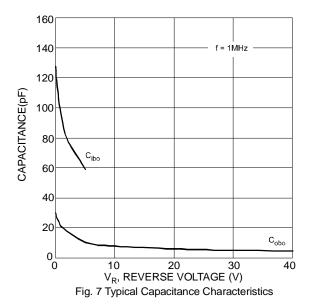


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





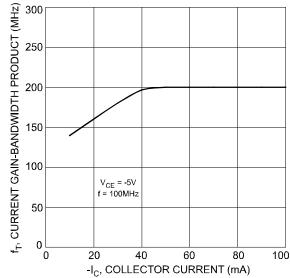


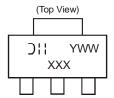
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DCP53-13	SOT-223	2500/Tape & Reel
DCP53-16-13	SOT-223	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

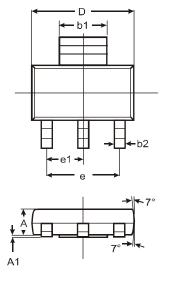


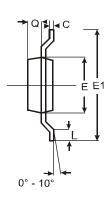
Office Manufacturer's code marking

XXX = Product type marking code Ex: P18 = DCP53 P18-16 = DCP53-16

YWW = Date code marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

Package Outline Dimensions

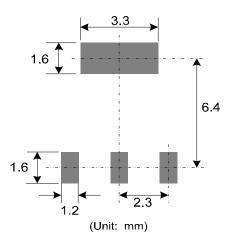




SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е			4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					



Suggested Pad Layout: (Based on IPC-SM-782)



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